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**OptiMOS™ 3 Power-Transistor**
**Features**

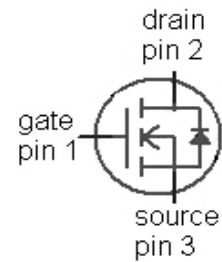
- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- N-channel, logic level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Halogen-free according to IEC61249-2-21

**Product Summary**

|                        |     |            |
|------------------------|-----|------------|
| $V_{DS}$               | 60  | V          |
| $R_{DS(on),max}$ (SMD) | 4.7 | m $\Omega$ |
| $I_D$                  | 80  | A          |



| Type           | IPB049N06L3 G | IPP052N06L3 G |
|----------------|---------------|---------------|
|                |               |               |
| <b>Package</b> | PG-TO263-3    | PG-TO220-3    |
| <b>Marking</b> | 049N06L       | 052N06L       |


**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                                    | Symbol         | Conditions                           | Value       | Unit               |
|--|----------------|--------------------------------------|-------------|--------------------|
| Continuous drain current                     | $I_D$          | $T_C=25\text{ °C}^{2)}$              | 80          | A                  |
|  |                | $T_C=100\text{ °C}$                  | 80          |                    |
| Pulsed drain current <sup>3)</sup>           | $I_{D,pulse}$  | $T_C=25\text{ °C}$                   | 320         |                    |
| Avalanche energy, single pulse <sup>4)</sup> | $E_{AS}$       | $I_D=80\text{ A}, R_{GS}=25\ \Omega$ | 77          | mJ                 |
| Gate source voltage                          | $V_{GS}$       |                                      | $\pm 20$    | V                  |
| Power dissipation                            | $P_{tot}$      | $T_C=25\text{ °C}$                   | 115         | W                  |
| Operating and storage temperature            | $T_j, T_{stg}$ |                                      | -55 ... 175 | $^{\circ}\text{C}$ |

<sup>1)</sup>J-STD20 and JESD22

<sup>2)</sup> Current is limited by bondwire; with an  $R_{th,jc}=1.3\text{ K/W}$  the chip is able to carry 114 A.

<sup>3)</sup> See figure 3 for more detailed information

<sup>4)</sup> See figure 13 for more detailed information

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|  |            |  |   |   |     |     |
|--|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case    | $R_{thJC}$ |  | - | - | 1.3 | K/W |
| Thermal resistance, junction - ambient | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|  |            | 6 cm <sup>2</sup> cooling area <sup>5)</sup> | - | - | 40  |     |

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |  |     |     |     |                  |
|----------------------------------|---------------|--|-----|-----|-----|------------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                                   | 60  | -   | -   | V                |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=58\text{ }\mu\text{A}$                             | 1.2 | 1.7 | 2.2 |                  |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$  | -   | 0.1 | 1   | $\mu\text{A}$    |
|                                  |               | $V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$ | -   | 10  | 100 |                  |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                                | -   | 1   | 100 | nA               |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=80\text{ A}$                                  | -   | 4.2 | 5   | $\text{m}\Omega$ |
|                                  |               | $V_{GS}=4.5\text{ V}, I_D=40\text{ A}$                                 | -   | 5.7 | 8.3 |                  |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=80\text{ A},$<br>(SMD)                        | -   | 3.9 | 4.7 |                  |
|                                  |               | $V_{GS}=4.5\text{ V}, I_D=40\text{ A},$<br>(SMD)                       | -   | 5.4 | 8   |                  |
| Gate resistance                  | $R_G$         |  | -   | 1.2 | -   | $\Omega$         |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max},$<br>$I_D=80\text{ A}$                   | 58  | 116 | -   | S                |

<sup>5)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |   |   |      |      |    |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=30\text{ V},$<br>$f=1\text{ MHz}$                    | - | 6300 | 8400 | pF |
| Output capacitance           | $C_{oss}$    |   | - | 1100 | 1500 |    |
| Reverse transfer capacitance | $C_{rss}$    |   | - | 47   | -    |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=80\text{ A}, R_G=3.3\ \Omega$ | - | 11   | -    | ns |
| Rise time                    | $t_r$        |   | - | 5    | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |   | - | 56   | -    |    |
| Fall time                    | $t_f$        |   | - | 12   | -    |    |

**Gate Charge Characteristics<sup>6)</sup>**

|                       |               |   |   |     |    |    |
|-----------------------|---------------|---|---|-----|----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=30\text{ V}, I_D=80\text{ A},$<br>$V_{GS}=0\text{ to }4.5\text{ V}$ | - | 23  | -  | nC |
| Gate to drain charge  | $Q_{gd}$      |   | - | 7   | -  |    |
| Switching charge      | $Q_{sw}$      |   | - | 19  | -  |    |
| Gate charge total     | $Q_g$         |   | - | 37  | 50 |    |
| Gate plateau voltage  | $V_{plateau}$ |   | - | 3.6 | -  |    |
| Output charge         | $Q_{oss}$     | $V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$                                     | - | 54  | 72 | nC |

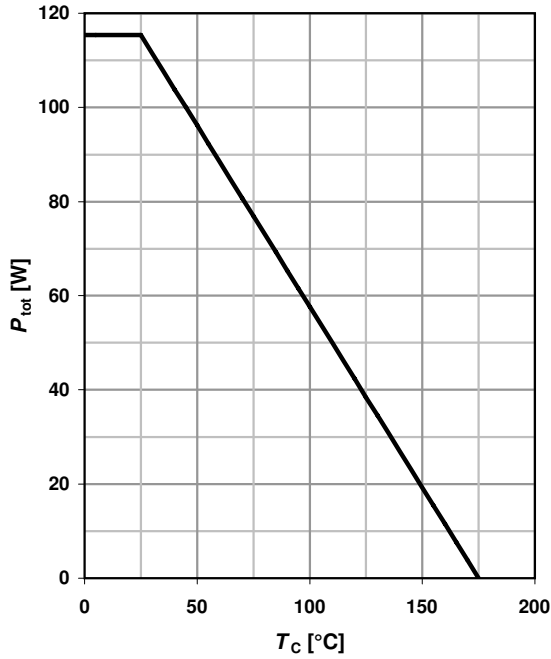
**Reverse Diode**

|                                  |               |   |   |     |     |    |
|----------------------------------|---------------|---|---|-----|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -   | 80  | A  |
| Diode pulse current              | $I_{S,pulse}$ |   | - | -   | 320 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=80\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$   | - | 1.0 | 1.2 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=30\text{ V}, I_F=80\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 48  | -   | ns |
| Reverse recovery charge          | $Q_{rr}$      |   | - | 60  | -   | nC |

<sup>6)</sup> See figure 16 for gate charge parameter definition

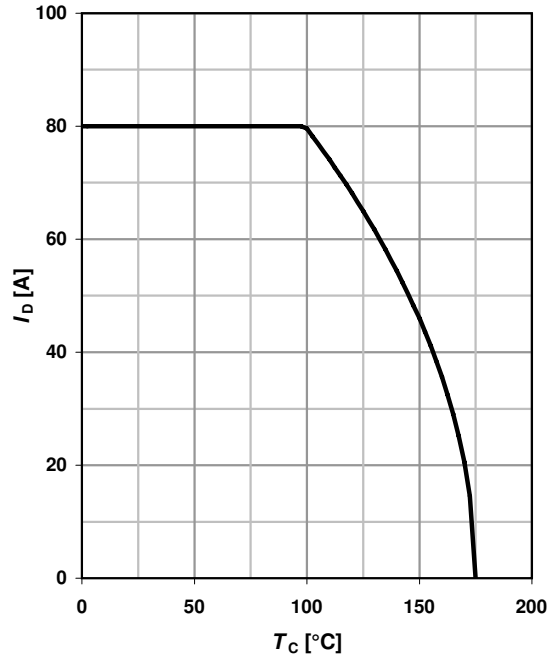
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

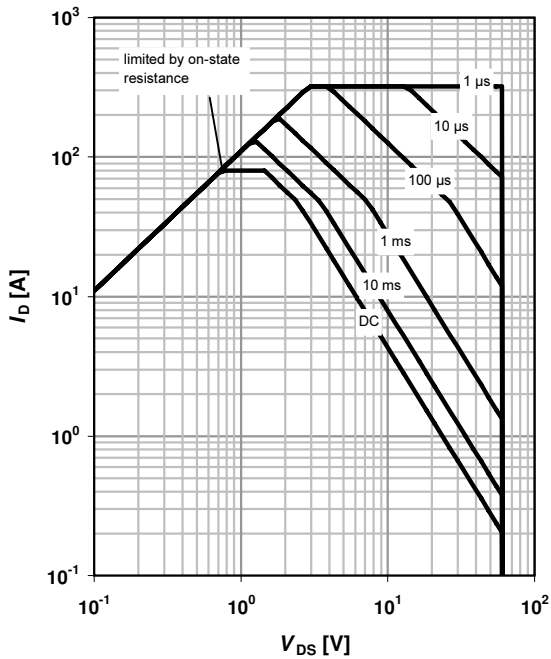
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

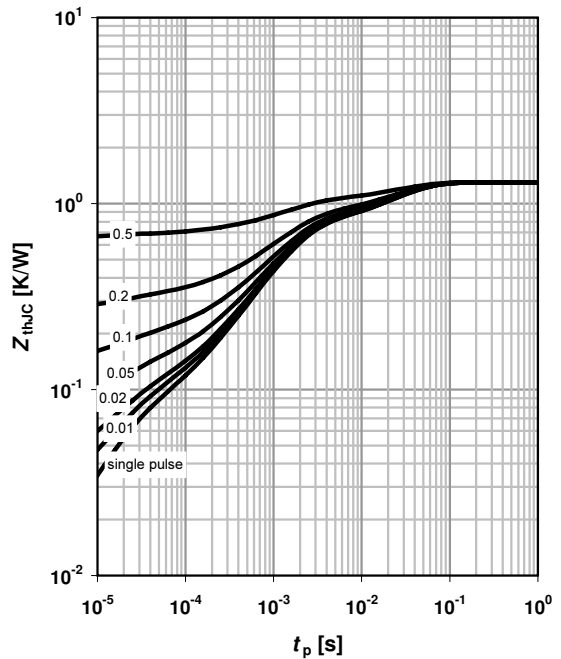
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

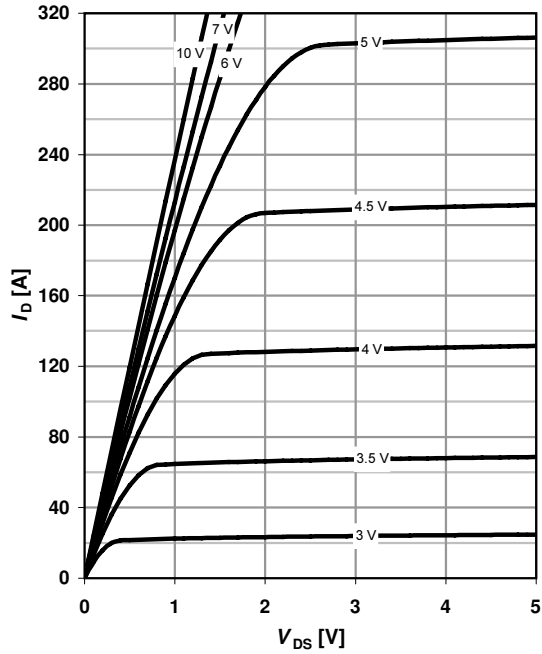
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

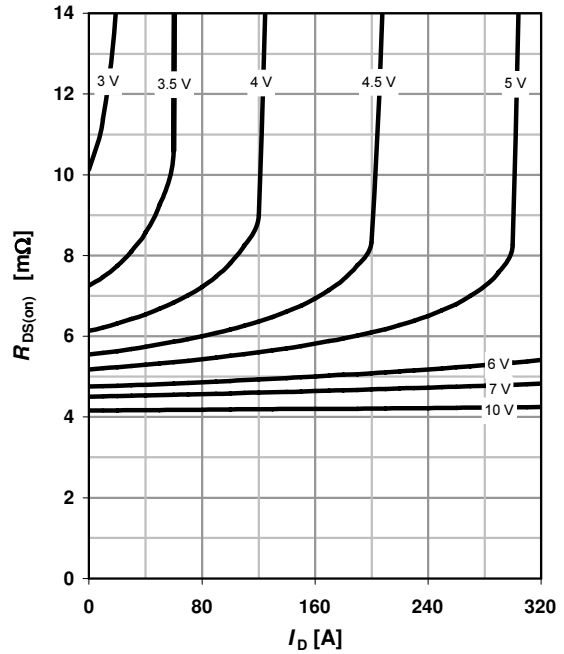
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

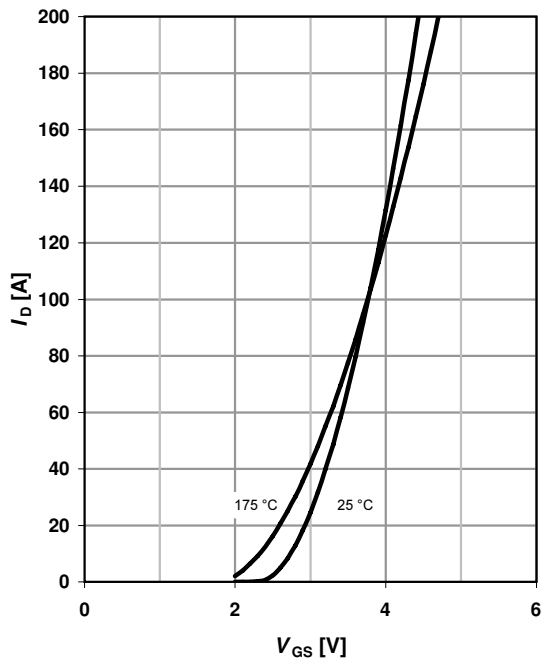
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

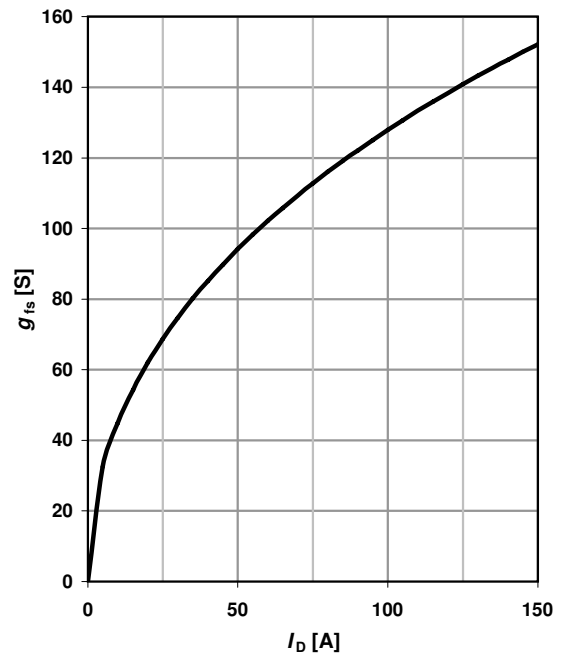
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



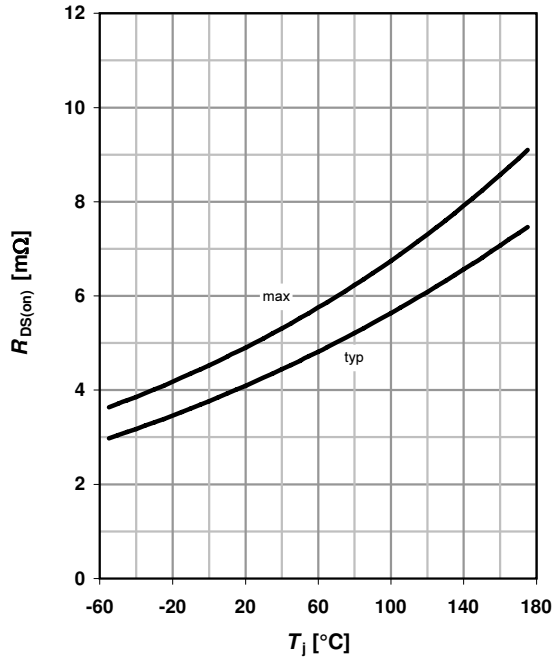
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

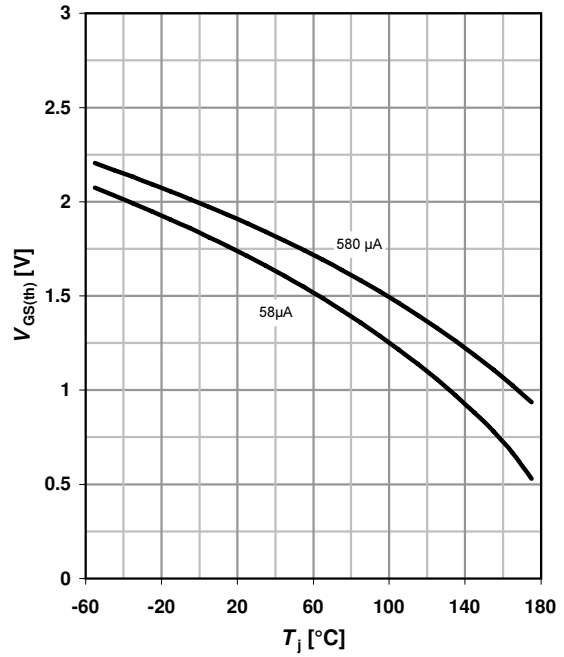
$R_{DS(on)} = f(T_j); I_D = 80 \text{ A}; V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

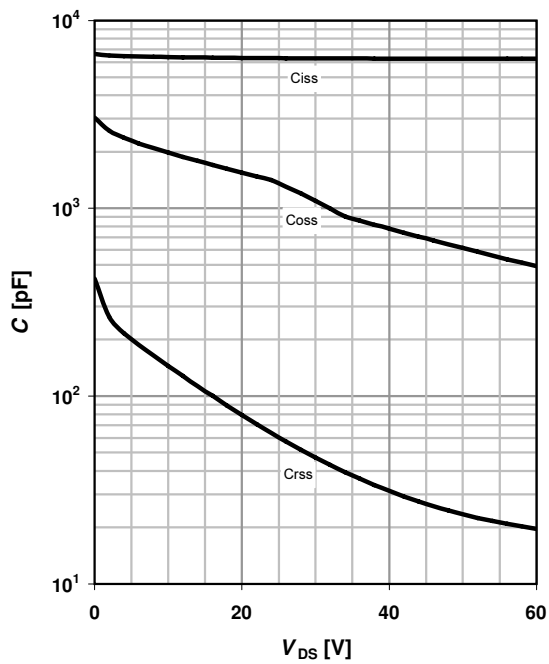
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

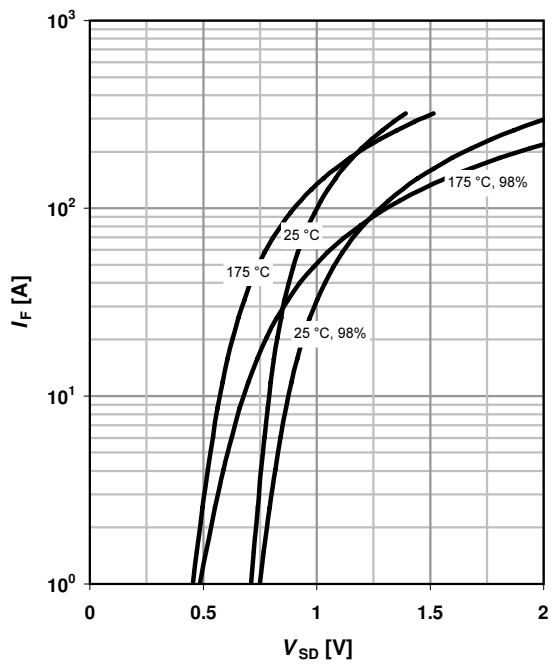
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

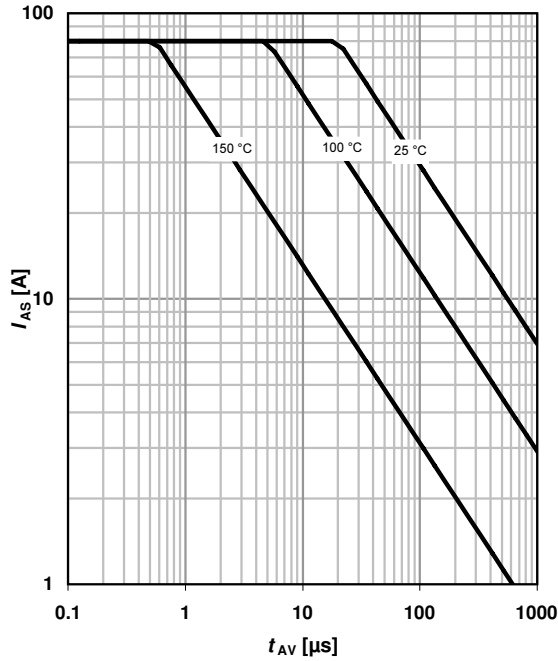
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

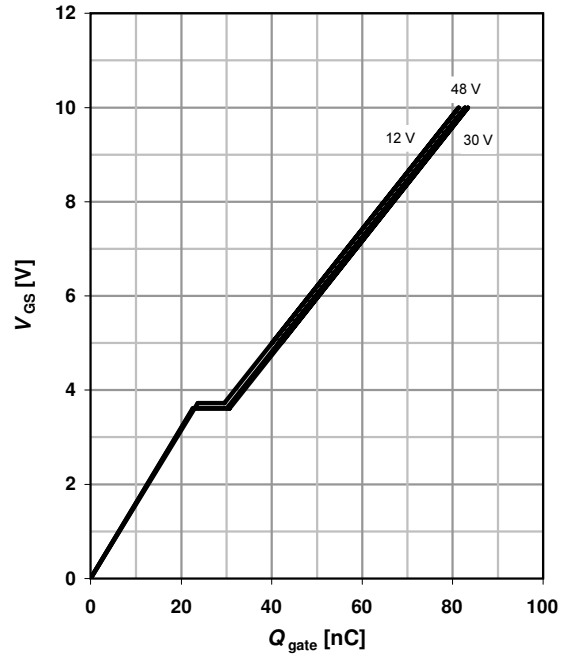
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

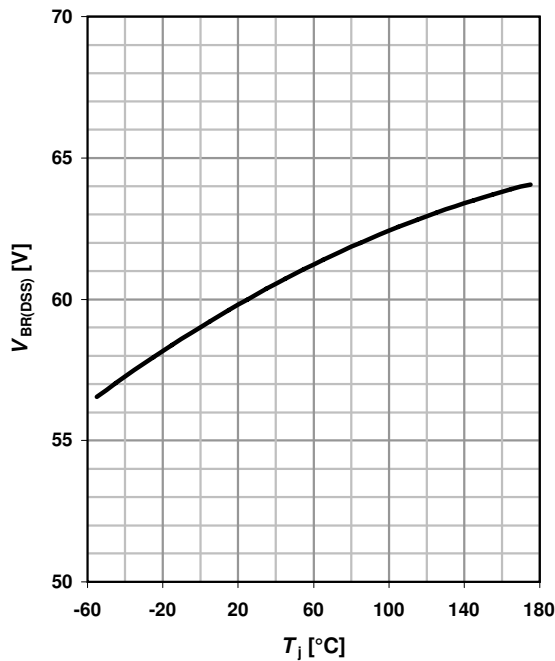
$V_{GS}=f(Q_{gate}); I_D=80 \text{ A pulsed}$

parameter:  $V_{DD}$

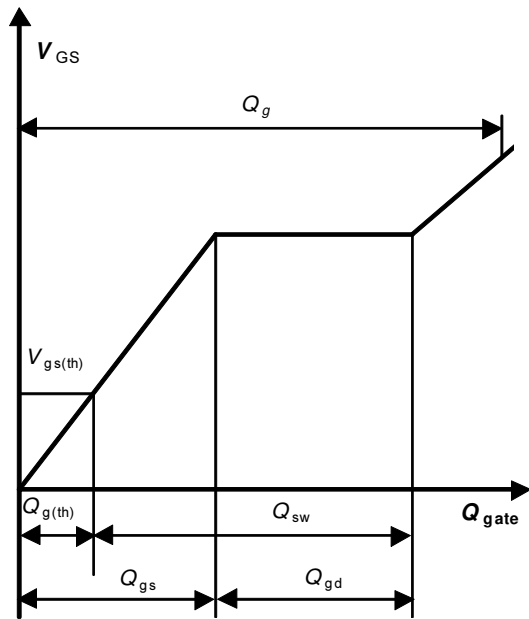


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

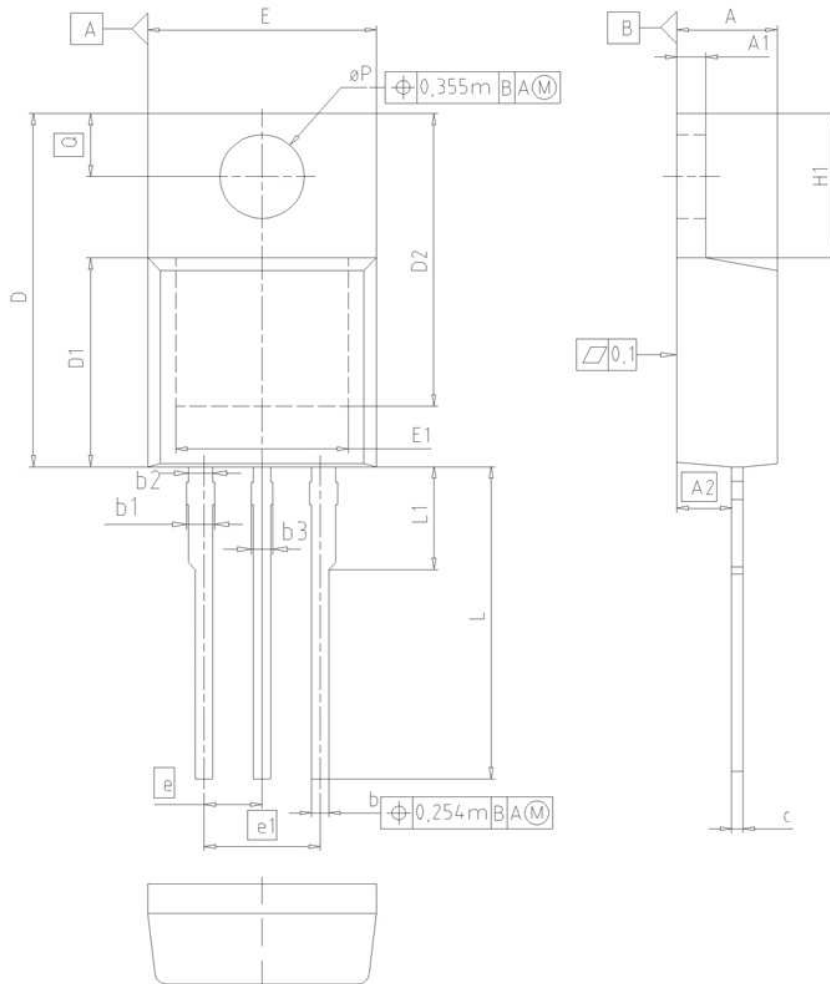


**16 Gate charge waveforms**





PG-TO220-3



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 1.17        | 1.40  | 0.046  | 0.055 |
| A2  | 2.15        | 2.72  | 0.085  | 0.107 |
| b   | 0.65        | 0.86  | 0.026  | 0.034 |
| b1  | 0.95        | 1.40  | 0.037  | 0.055 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| b3  | 0.65        | 1.15  | 0.026  | 0.045 |
| c   | 0.33        | 0.60  | 0.013  | 0.024 |
| D   | 14.81       | 15.95 | 0.583  | 0.628 |
| D1  | 8.51        | 9.45  | 0.335  | 0.372 |
| D2  | 12.19       | 13.10 | 0.480  | 0.516 |
| E   | 9.70        | 10.36 | 0.382  | 0.408 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 3           |       | 3      |       |
| H1  | 5.90        | 6.90  | 0.232  | 0.272 |
| L   | 13.00       | 14.00 | 0.512  | 0.551 |
| L1  | -           | 4.80  | -      | 0.189 |
| øP  | 3.60        | 3.89  | 0.142  | 0.153 |
| Q   | 2.60        | 3.00  | 0.102  | 0.118 |

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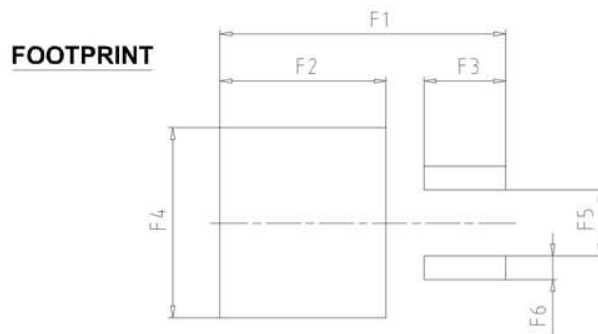
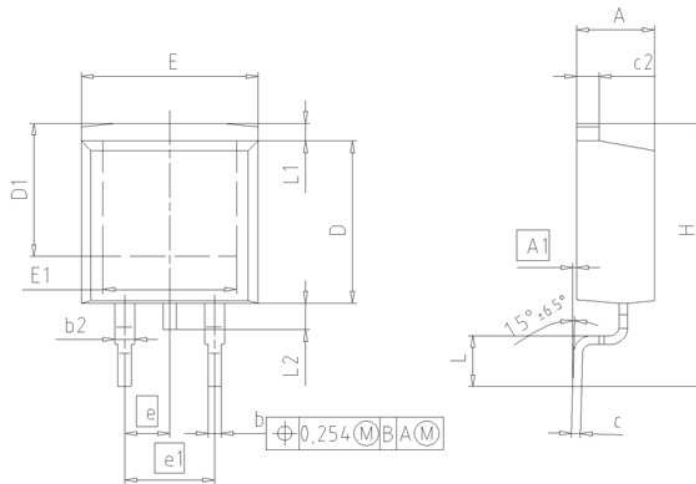
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PG-TO263 (D<sup>2</sup>-Pak)



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 0.00        | 0.25  | 0.000  | 0.010 |
| b   | 0.65        | 0.85  | 0.026  | 0.033 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| c   | 0.33        | 0.65  | 0.013  | 0.026 |
| c2  | 1.17        | 1.40  | 0.046  | 0.055 |
| D   | 8.51        | 9.45  | 0.335  | 0.372 |
| D1  | 7.10        | 7.90  | 0.280  | 0.311 |
| E   | 9.80        | 10.31 | 0.386  | 0.406 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 2           |       | 2      |       |
| H   | 14.61       | 15.88 | 0.575  | 0.625 |
| L   | 2.29        | 3.00  | 0.090  | 0.118 |
| L1  | 0.70        | 1.60  | 0.028  | 0.063 |
| L2  | 1.00        | 1.78  | 0.039  | 0.070 |
| F1  | 16.05       | 16.25 | 0.632  | 0.640 |
| F2  | 9.30        | 9.50  | 0.366  | 0.374 |
| F3  | 4.50        | 4.70  | 0.177  | 0.185 |
| F4  | 10.70       | 10.90 | 0.421  | 0.429 |
| F5  | 3.65        | 3.85  | 0.144  | 0.152 |
| F6  | 1.25        | 1.45  | 0.049  | 0.057 |

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